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DUAL P-CHANNEL ENHANCEMENT MODE MOSFETS

Part No.	V <sub>(BR)DSS</sub> Volts Max	V <sub>(BR)DC</sub> Volts Max	Power Dissipation Free Air mW	I <sub>SSP</sub> nA Typ	I <sub>D(on)</sub> mA Typ	V <sub>GS(th)</sub> Volts Min/Max	r <sub>DS(on)</sub> Ohms Typ	Y <sub>f</sub> μmho Typ	C <sub>iss</sub> pF Typ	C <sub>rss</sub> pF Typ	Y <sub>f</sub> Ratio Typ	•V <sub>G15</sub> —V <sub>G25</sub> mV Typ	•V <sub>G15</sub> —V <sub>G25</sub> •T <sub>11</sub> /V/°C Typ	Case P.18	Lead Con- fig. P.20
* MEM 550	-30	-30	112	-0.1*	-5	-3/-6	250	1,500	1.1	1.1	0.85	70	—	6	7
* MEM 550C	-25	-25	85	-0.2*	-5	-3/-6	250	800	2.0	2.0	0.8	100	—	6	7
MEM 551	-30	-40	112	-0.03 pA	-5	-3/-6	250	1,000	1.1	1.1	0.9	70	—	6	7
MEM 551C	-25	-25	85	-1.0 pA	-5	-3/-6	250	750	1.5	1.5	0.85	70	—	6	7
#* MEM 954	-30	-30	112	-0.03*	—	-2.5/-5.0	45	1,000	2.0	1.5	0.95	50	75	6	7
* MEM 954A	-30	-30	112	-0.03*	—	-2.0/-5.0	100	1,000	2.0	1.5	0.95	15	25	6	7
* MEM 954B	-30	-30	112	-0.03*	—	-2.0/-5.0	100	1,000	2.0	1.5	0.95	5	15	6	7
# MEM 955	-35	-40	112	-0.02 pA	—	-2.0/-5.0	100	1,000	2.0	1.5	0.95	50	75	6	7
MEM 955A	-35	-40	112	-0.02 pA	—	-2.0/-5.0	100	1,000	2.0	1.5	0.95	15	25	6	7
MEM 955B	-35	-40	112	-0.02 pA	—	-2.0/-5.0	100	1,000	2.0	1.5	0.95	5	15	6	7
2N 3609	-25	-25	350	-0.02	-3.25	-4.0/-6.0	450	1,000	—	1.0	1.0	100	—	6	8
2N 4066	-30	-40	112	-0.5	-32	-3/-6	300	2,900	4.0	0.6	0.85	100	—	5	9
2N 4067	-30	-40	112	-0.5	-32	-3/-6	125	4,200	4.0	0.6	0.6	70	—	5	9
3N 147	-30	-40	150	-1.0	-32	-2.0/-6.0	300	3,000	4.0	0.6	0.85	90	—	5	1
3N 148	-30	-40	150	-1.0	-32	-2.0/-6.0	300	3,000	4.0	0.6	0.85	100	—	5	1
*3N 151	-30	-30	162	-0.05*	-7	-3/-6	250	2,000	5.0	2.0	0.9	250	—	6	7
*3N 165	-40	-40	300	-0.05*	-15	-3.0/-6.5	250	2,000	2.5	0.7	0.9	100	—	8	9
*3N 166	-40	-40	300	-0.05*	-15	-2.0/-5.0	250	2,000	2.5	0.7	—	—	—	8	9
*3N 188	-40	-40	300	-0.1*	-15	-2.0/-5.0	200	2,500	2.0	1.5	0.9	50	50 μV	6	7
*3N 189	-40	-40	300	-0.1*	-15	-2.0/-5.0	200	2,500	2.0	1.5	—	—	—	6	7
3N 190	-40	-40	300	-1 pA	-15	-2.0/-5.0	200	2,500	2.0	1.5	0.9	50	50 μV	6	7
3N 191	-40	-40	300	-1 pA	-15	-2.0/-5.0	200	2,500	2.0	1.5	—	—	—	6	7
MEM 517C2M	-25	-25	350	-1.0	-50	-2.5/-5.0	45	12,000	10	—	—	—	—	7	33

N-CHANNEL ENHANCEMENT MODE MOSFETS

Part No.	Structure	Power 25°C Amb mW Max	V <sub>(BR)DSS</sub> Volts Max	V <sub>(BR)DSS</sub> Volts Max	V <sub>(BR)DC</sub> Volts Max	I <sub>SS</sub> nA Typ	I <sub>SSP</sub> nA Typ	I <sub>D(on)</sub> mA Typ	V <sub>GS(th)</sub> Volts Min/Max	r <sub>DS(on)</sub> Ohms Typ	Y <sub>f</sub> μmho Typ	C <sub>iss</sub> pF Typ	C <sub>rss</sub> pF Typ	T <sub>on</sub> nsec Typ	T <sub>off</sub> nsec Typ	Case P.19	Lead Con- fig. P.20
MEM 562	Triode	225	20	±30	±30	1	1 pA	15	0.5/4.0	150	2,500	3.0	0.3	35	60	4	3
MEM 562C	Triode	175	20	±30	±30	2	10 pA	15	0.5/4.0	150	2,000	3.0	0.5	40	60	4	3
MEM 563	Triode	225	20	±30	±30	1	1 pA	40	0.5/4.0	40	5,000	4.0	0.3	20	60	4	3
# MEM 563C	Triode	175	20	±30	±30	3	10 pA	40	0.5/4.0	50	4,000	4.0	0.4	20	60	4	3
* MEM 660	Triode <sup>h</sup>	150	20	±30	±30	—	—	60	-0.3/-4	30	10,000	4.5	0.3	10	60	4	2
#* MEM 711	Triode	225	25	±30	±30	1	0.1*	40	0.5/1.5	50	3,000	4.5	0.5	10	65	4	3
#* MEM 712	Triode	200	25	±30	±30	1	.01	40	0.5/2.0	50	2,500	4.5	0.5	15	70	10	3
2N 4038	Triode	150	15	±50	±50	100	—	—	-/-2*	—	2,000	3.0	0.2	—	—	4	3
2N 4351	Triode	225	25	±25	±25	5	5 pA	1.5	1.0/5.0	150	2,500	2.5	0.7	30	60	4	3
3N 169	Triode	300	25	±35	±35	10	0.01	8 mA	0.5/1.5	150	4,000	5.0	1.3	20	65	4	3
3N 170	Triode	300	25	±35	±35	10	0.01	8 mA	1.0/2.0	150	4,000	5.0	1.3	20	70	4	3
3N 171	Triode	300	25	±35	±35	10	0.01	8 mA	1.5/3.0	150	4,000	5.0	1.3	20	70	4	3
3N 175	Triode	225	30	±35	±35	1	10 pA	25	1.0/2.0	120	2,500	3.0	0.3	25	70	4	3
3N 176	Triode	225	25	±30	±25	3	30 pA	20	1.0/2.5	200	2,000	4.0	0.4	35	70	4	3
3N 177	Triode	225	20	±30	±30	5	50 pA	15	1.0/3.5	300	1,500	5.0	0.5	35	70	4	3

\* Diode Protected Gate.

• V<sub>GS</sub> (cutoff).

<sup>h</sup> V<sub>SD</sub> applied for enhancement mode operation.

■ Specified in four (4) resistance ranges.

# Preferred type. Available from stock.

\* Grille protégée par diode.

• V<sub>GS</sub> (coupe).

<sup>h</sup> V<sub>SD</sub> appliqué en mode à enrichissement.

■ Spécifié dans quatre (4) gammes de

résistance.

# Type preferable. Disponible au magasin.

\* Gate mit Diode geschützt.

• V<sub>GS</sub> Abschürspannung.

<sup>h</sup> V<sub>SD</sub> für Betrieb im Anreicherungsereich

eingestellt.

■ Eingeteilt in 4 Widerstandsbereiche.

# Vorzugstyp. Ab Lager lieferbar.